

PMBT4403

FEATURES

- High current (max. 600 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- Industrial and consumer switching applications.

DESCRIPTION

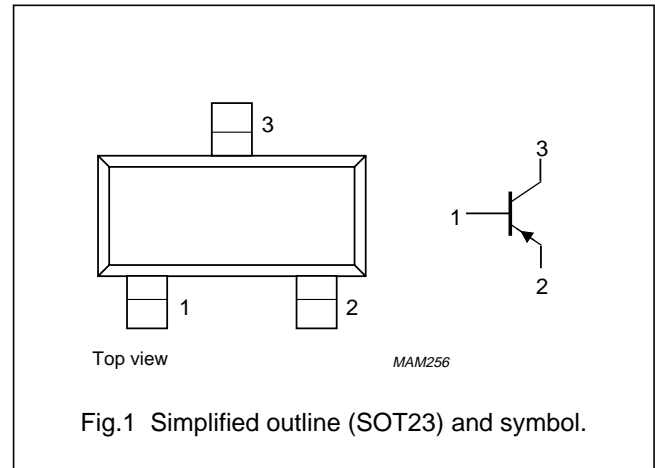
PNP switching transistor in a SOT23 plastic package.
NPN complement: PMBT4401.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
PMBT4403	*2T

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–40	V
V_{CEO}	collector-emitter voltage	open base	–	–40	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–600	mA
I_{CM}	peak collector current		–	–800	mA
I_{BM}	peak base current		–	–200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS
 $T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -40\text{ V}$	–	–50	nA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -5\text{ V}$	–	–50	nA
h_{FE}	DC current gain	$V_{CE} = -1\text{ V}$; (see Fig.2) $I_C = -0.1\text{ mA}$	30	–	
		$I_C = -1\text{ mA}$	60	–	
		$I_C = -10\text{ mA}$	100	–	
		$V_{CE} = -2\text{ V}$ $I_C = -150\text{ mA}$	100	300	
		$I_C = -500\text{ mA}$	20	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -150\text{ mA}; I_B = -15\text{ mA}$	–	–400	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	–	–750	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -150\text{ mA}; I_B = -15\text{ mA}$	–	–950	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	–	–1.3	V
C_c	collector capacitance	$I_E = I_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	–	8.5	pF
C_e	emitter capacitance	$I_C = I_c = 0; V_{EB} = -500\text{ mV}; f = 1\text{ MHz}$	–	35	pF
f_T	transition frequency	$I_C = -20\text{ mA}; V_{CE} = -10\text{ V}; f = 100\text{ MHz}$	200	–	MHz
Switching times (between 10% and 90% levels); (see Fig.3)					
t_{on}	turn-on time	$I_{Con} = -150\text{ mA}; I_{Bon} = -15\text{ mA};$ $I_{Boff} = 15\text{ mA}$	–	40	ns
t_d	delay time		–	15	ns
t_r	rise time		–	30	ns
t_{off}	turn-off time		–	350	ns
t_s	storage time		–	300	ns
t_f	fall time		–	50	ns